

N-channel 40 V, 11 mΩ logic level MOSFET in LFPAK33 19 September 2016

Product data sheet

1. **General description**

Logic level N-channel MOSFET in an LFPAK33 (Power33) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. **Features and benefits**

- Q101 compliant •
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating •
- True logic level gate with V_{GS(th)} rating of greater than 0.5 V at 175 °C

Applications 3.

- 12 V automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching •

Quick reference data 4.

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	-	40	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>	-	-	53	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	-	62	W
Static charact	eristics					
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 15 A; T _j = 25 °C; <u>Fig. 11</u>	-	9.3	11	mΩ
Dynamic char	acteristics					
Q _{GD}	gate-drain charge	I_D = 15 A; V_{DS} = 32 V; V_{GS} = 5 V; T_j = 25 °C; Fig. 13; Fig. 14	-	5	-	nC

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	Source		D
2	S	Source		
3	S	Source	\bigcirc	G-UF4
4	G	Gate		mbb076 S
mb	D	Mounting base; connected to drain	LFPAK33 (SOT1210)	

6. Ordering information

Table 3. Ordering information							
Type number	Package	ckage					
	Name	Description	Version				
BUK9M11-40E	LFPAK33	Plastic single ended surface mounted package (LFPAK33); 8 leads	SOT1210				

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK9M11-40E	91140E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	40	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	40	V
V _{GS}	gate-source voltage	DC; T _j ≤ 175 °C		-10	10	V
		Pulsed; T _j ≤ 175 °C	[1][2]	-15	15	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	62	W
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	53	А
		V _{GS} = 5 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	37	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$; Fig. 3		-	211	А

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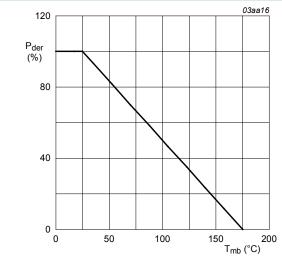
Symbol	Parameter	Conditions		Min	Max	Unit
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-dra	in diode					
I _S	source current	T _{mb} = 25 °C		-	51	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	211	А
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} & {\sf I}_{\sf D} = 53 \; {\sf A}; {\sf V}_{\sf sup} \le 40 \; {\sf V}; {\sf R}_{\sf GS} = 50 \; \Omega; \\ & {\sf V}_{\sf GS} = 5 \; {\sf V}; \; {\sf T}_{\sf j(init)} = 25 \; {\rm ^{\circ}C}; \; {\sf unclamped}; \\ & {\sf Fig. 4} \end{split}$	[3][4]	-	32.4	mJ

[1] Accumulated pulse duration up to 50 hours delivers zero defect ppm.

[2] Significantly longer life times are achieved by lowering T_i and or V_{GS}

[3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[4] Refer to application note AN10273 for further information.





$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

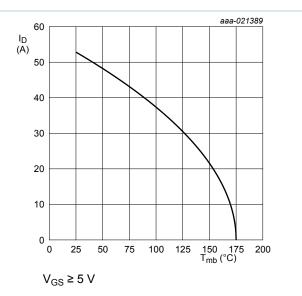
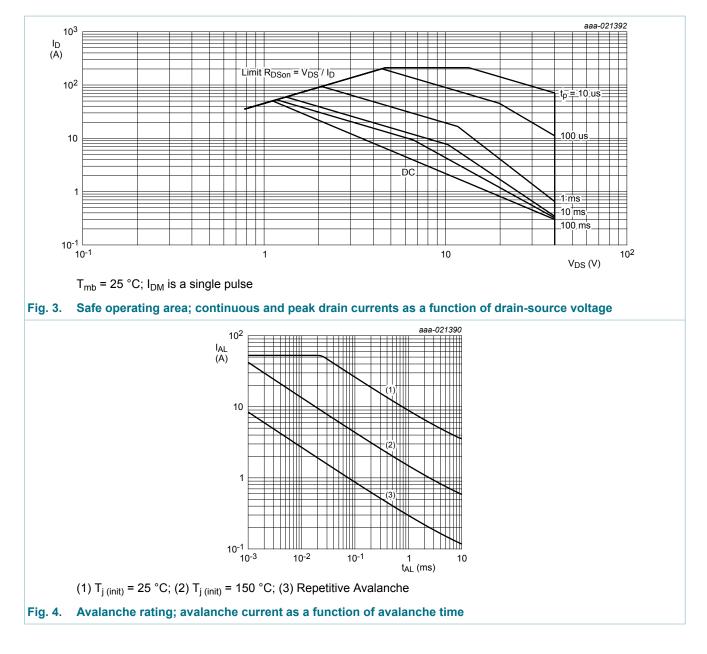


Fig. 2. Continuous drain current as a function of mounting base temperature

$$I_D = 53A \times \sqrt{\frac{175^{\circ}C - T_{mb}}{150^{\circ}C}} \text{ for } T_{mb} \ge 25^{\circ}C$$

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9. Thermal characteristics

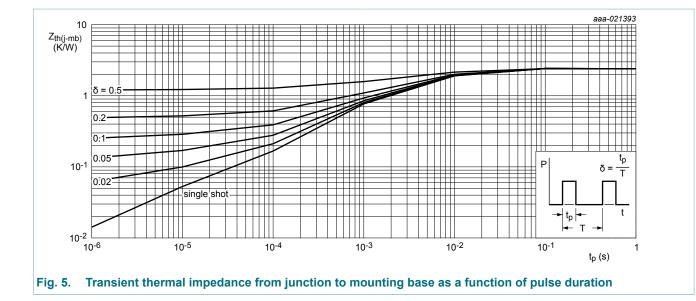
Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. <u>5</u>	-	2.01	2.43	K/W

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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	40	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	36	-	-	V
V _{GS(th)} gate-source threshold voltage	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 9; Fig. 10	1.4	1.7	2.1	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; Fig. 10	-	-	2.45	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 10	0.5	-	-	V
I _{DSS}	DSS drain leakage current	V_{DS} = 40 V; V_{GS} = 0 V; T_j = 25 °C	-	0.01	1	μA
		V _{DS} = 40 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
I _{GSS} gate leaka	gate leakage current	V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 5 V; I _D = 15 A; T _j = 25 °C; <u>Fig. 11</u>	-	9.3	11	mΩ
	resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; Fig. 11	-	7.5	9	mΩ
		V _{GS} = 5 V; I _D = 15 A; T _j = 175 °C; Fig. 12	-	-	22	mΩ
Dynamic cl	naracteristics		ł	1	_	
Q _{G(tot)}	total gate charge	I_D = 15 A; V_{DS} = 32 V; V_{GS} = 5 V;	-	13.4	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13; Fig. 14</u>	-	3.5	-	nC

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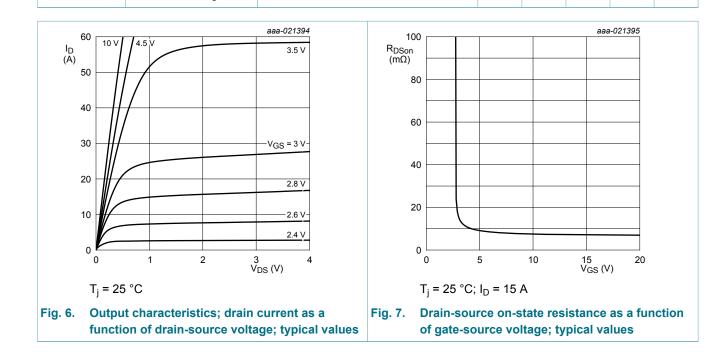
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Qr

recovered charge

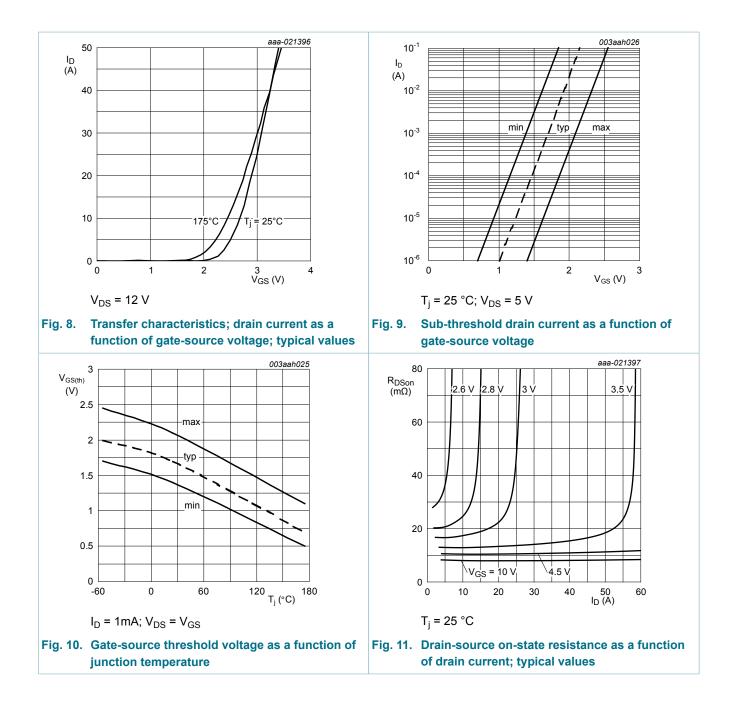
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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Q _{GD}	gate-drain charge		-	5	-	nC
C _{iss}	input capacitance	V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz;	-	1294	1721	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	175	210	pF
C _{rss}	reverse transfer capacitance		-	91	125	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 2 \Omega; \text{ V}_{GS} = 5 \text{ V};$ $R_{G(ext)} = 5 \Omega; \text{ T}_{j} = 25 \text{ °C}$	-	9.3	-	ns
t _r	rise time		-	15.2	-	ns
t _{d(off)}	turn-off delay time		-	19	-	ns
t _f	fall time		-	12.2	-	ns
Source-dra	in diode	· · · · · ·				
V _{SD}	source-drain voltage	I_{S} = 15 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	I _S = 15 A; dI _S /dt = -100 A/μs; V _{GS} = 0 V;	-	17.7	-	ns
Qr	recovered charge	V _{DS} = 25 V; T _j = 25 °C	_	9.8	_	nC



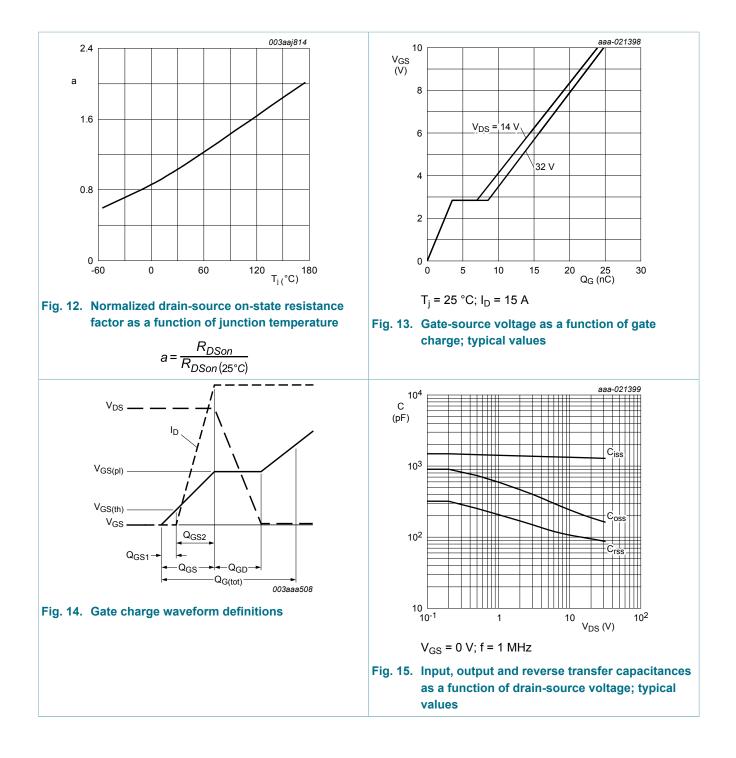
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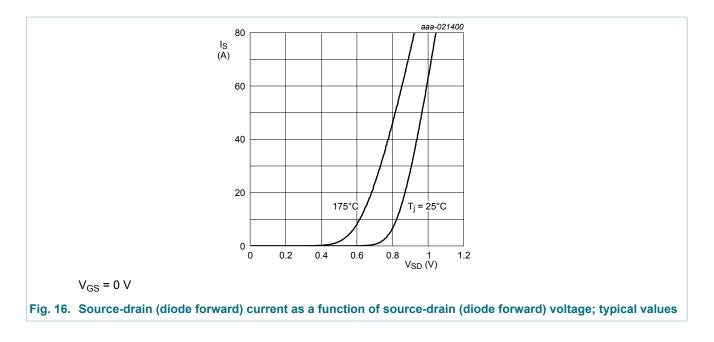


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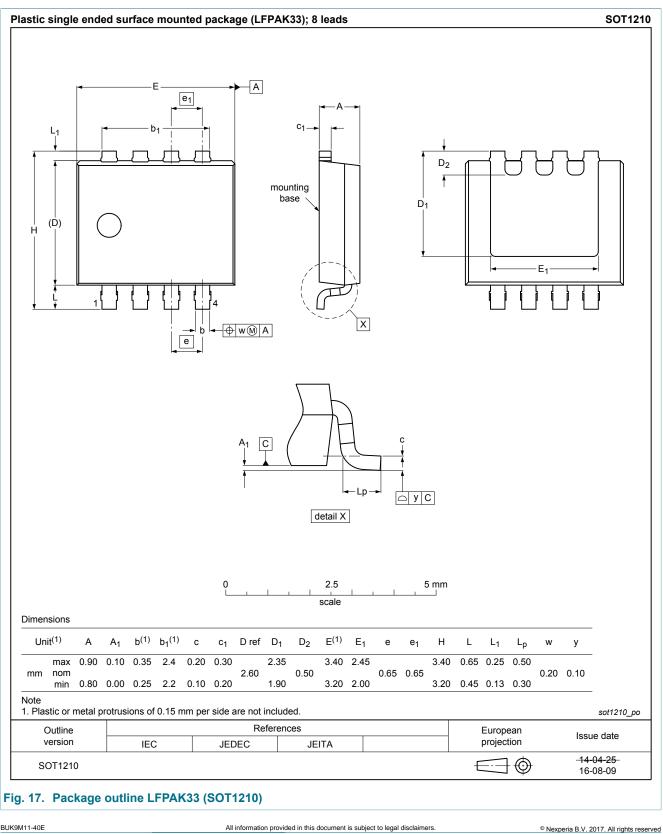


11. Application information

For guidance on how to use and understand this datasheet, please refer to application note <u>AN11158</u> "Understanding power MOSFET datasheet parameters".

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12. Package outline



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13. Legal information

13.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

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